



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Shunpei YAMAZAKI et al. )  
Serial No. 08/799,506 )  
Filed: February 12, 1997 )  
For: METHOD OF PROCESSING )  
SEMICONDUCTOR DEVICE )  
APPARATUS FOR PROCESSING A )  
SEMICONDUCTOR AND APPARATUS )  
FOR PROCESSING SEMICONDUCTOR )  
DEVICE )

Art Unit: 2822

Examiner: M. Wilczewski

**CERTIFICATE OF MAILING**

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*Adrian M. Stamps*

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing information known to Applicant and requests that this information be made of record in the above identified application. Copies are submitted herewith in accordance with 37 C.F.R. 1.98(a).

Except as provided below, in accordance with 37 C.F.R. § 1.97(e), it is certified that either (1) each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this information disclosure statement, or (2) no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign patent application and no item of information contained in the information disclosure statement was known to any individual designated in 37 C.F.R. § 1.56(c) more than three months prior to the filing of this information disclosure statement.

The enclosed references were cited in a rejection by the Japanese Patent Office in a counterpart Japanese application. The rejection has the following comments.

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With respect to claims 1-5. When comparing an invention claimed in claim 1 of the present application with Japanese Patent Laid-Open No. 63-318125 (This is referred to as cited document 1 hereinafter. Particularly see from page 3, upper left column, line 4 to page 4, upper right column, line 13.), they are different in five points as follows.

- (A) In the invention claimed in claim 1 in the present application, a semiconductor film formed on a glass substrate is used for a channel region of a transistor. On the contrary, in an invention described in the cited document 1, a semiconductor substrate itself is used for a channel region of a transistor.
- (B) In the invention claimed in claim 1 in the present application, an N-type impurity is doped. On the contrary, in the invention described in the cited document 1, a P-type impurity is doped.
- (C) In the invention claimed in claim 1 in the present application, a gate insulating film in an ion implantation area is removed by dry etching. On the contrary, in the invention described in the cited document 1, a gate insulating film in an ion implantation area is removed by wet etching.
- (D) In the invention claimed in claim 1 in the present application, a semiconductor treatment apparatus used in the invention has a first chamber for doping and a second chamber for etching and a third chamber for a laser light irradiation. Further, in the invention claimed in claim 1 in the present application, a treatment substrate is transferred among these chambers without exposing the

treatment substrate to an outside air. On the contrary, in the invention described in the cited document 1, it is not expressly described that a treatment substrate is transferred among chambers without exposing the treatment substrate to an outside air.

- (E) In the invention claimed in claim 1 in the present application, a laser light is irradiated after etching an insulating film. On the contrary, in an invention described in the cited document 1, a lamp annealing is conducted after etching an insulating film.

The above different points are considered as follows.

With respect to the different points (A) to (C). It is a known technology before filing the present application to use a semiconductor layer formed on a glass substrate for MOS transistor, and to use a dry etching method causing a discharge for an etching method of an insulating film, and to form an N-type transistor doped with an N-type impurity.

With respect to the different point (D). It is a known technology before filing the present application to form a semiconductor device by using a multi-chamber for conducting a successive process without exposing to an outside air to conduct a heat treatment process such as film formation, crystallization or an impurity activation and to conduct an etching, in order to prevent a treatment substrate from being polluted, as described in "NIKKEI MICRO DEVICE, October, 1989" (This is referred to as cited document 2 hereinafter. Particularly see from page 34 to page 39) cited in the prior rejection and in Japanese Patent Laid-Open No.4-251921 (This is referred to as cited reference 3 hereinafter. Particularly see from the first paragraph to the 41<sup>st</sup> paragraph) cited in the prior rejection. It is an implementable matter by ordinary skill in the art as

occasion demands to conduct steps such as an impurity doping and an insulating film etching and an impurity activation described in the cited document 1 by using a multi-chamber.

With respect to the different point (E). It is merely a known technology before filing the present application to conduct an impurity activation by a laser light, as described for example in Japanese Patent Laid-Open No. 4-221854 (This is referred to as cited document 4 hereinafter. Particularly see the 38<sup>th</sup> paragraph.) cited in the prior rejection and in Japanese Patent Laid-Open No. 3-201528 (This is referred to as cited document 5 hereinafter. Particularly see from page 3, lower left column, line 4 to page 3, lower left column, line 16) cited in the prior rejection.

The same is applied to claims 2-5.

In this way, the invention claimed in claims 1-5 of the present application involves a matter easily made by one of ordinary skill in the art from the cited document 1 and the above know technologies.

With respect to claim 6. It is merely a known technology before filing the present application to form a mask comprising a resist mask over a first gate electrode so as to cover a first active layer, to conduct a first ion implantation using a second gate electrode provided over a second active layer as a mask, and to conduct a second ion implantation using the first gate electrode over the first active layer and the second gate electrode over the second active layer as masks after removing the resist film over the first gate electrode, as described for example in Japanese Patent Laid-Open No. 3-42868 (This is referred to as cited document 6 hereinafter. Particularly see from page 3, lower left column, line 3 to page 4, upper right column, line 12.) and in Japanese Patent Laid-Open No. 3-

95965 (This is referred to as cited document 7 hereinafter. Particularly see from page 2, upper left column, line 15 to page 2, lower left column, line 15).

In addition, it is a known technology before filing the present application to conduct a resist removal by a chamber.

With respect to claim 7, it is described in the cited document 5 to conduct an impurity activation by an excimer laser.

With respect to claim 8, it is merely a known technology before filing the present application to use a liner laser light for a shape of a laser light and to irradiate with a substrate scanned.

In this way, the invention as claimed in claims 1-8 of the present application can be easily invented by one of skill in the art, based on the cited references 1-7.

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U.S. Patent No. 5,316,960 is in the family of JP 03-042868. This U.S. Patent was not directly cited by the Japanese Patent Office, but is submitted herewith for consideration by the Examiner.

Respectfully submitted,



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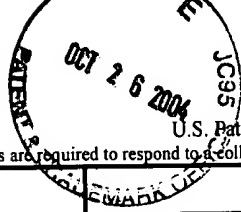
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PTO/SB/08A (08-00)

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				Application Number	08/799,506
				Filing Date	February 12, 1997
				First Named Inventor	Shunpei YAMAZAKI et al.
				Group Art Unit	2822
				Examiner Name	M. Wilczewski
Sheet	1	of	1	Attorney Docket Number	0756-1630

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
		5,316,960		Watanabe et al.	05/31/1994	

FOREIGN PATENT DOCUMENTS								
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
		JP	03-042868			02/25/1991		Abst.
		JP	03-095965			04/22/1991		Abst.

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>2</sup>

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**TRANSMITTAL  
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(to be used for all correspondence after initial filing)

<b>TRANSMITTAL FORM</b>  (to be used for all correspondence after initial filing)	Application Number	08/799,506
	Filing Date	February 12, 1997
	First Named Inventor	Shunpei YAMAZAKI et al.
	Group Art Unit	2822
	Examiner Name	M. Wilczewski
Total Number of Pages in This Submission	Attorney Docket Number	0756-1630

**ENCLOSURES (check all that apply)**

<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input checked="" type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input type="checkbox"/> Information Disclosure Statement <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Declaration and Power of Attorney <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s) _____	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences <input type="checkbox"/> Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) <input type="checkbox"/> Proprietary Information <input type="checkbox"/> Status Letter <input type="checkbox"/> Other Enclosures 1. 2. 3. 4. 5. 6.
Remarks <input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. 50-2280 for the above identified docket number.		

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